

Supporting Information

Low-Temperature Thermally-Annealed Niobium
Oxide Thin Films as a Minimally Color Changing
Ion Storage Layer in Solution-Processed Polymer
Electrochromic Devices

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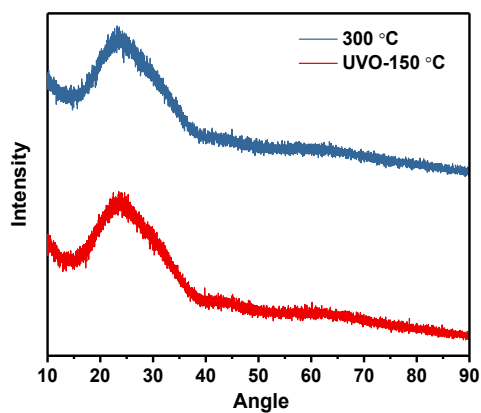


Figure S1. X-ray diffraction patterns of UVO-150 °C and 300 °C annealed a-Nb₂O₅ thin films.

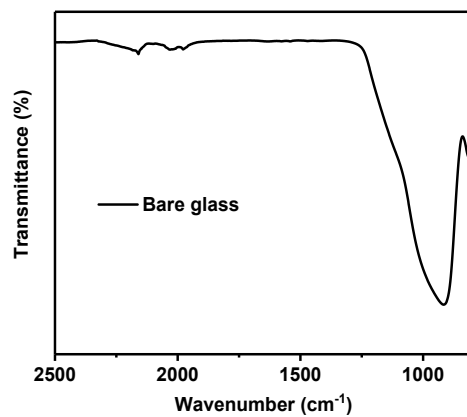


Figure S2. FTIR spectrum of a bare glass substrate.

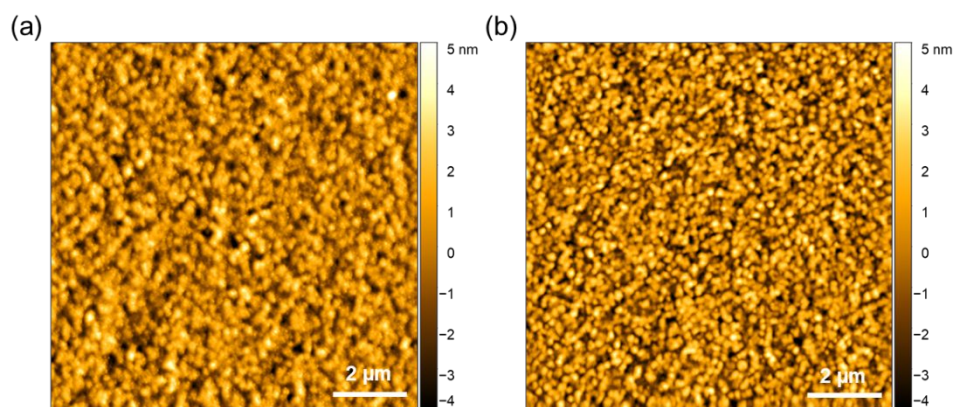


Figure S3. AFM images of the a-Nb₂O₅ thin films (a) before and (b) after UVO treatment.

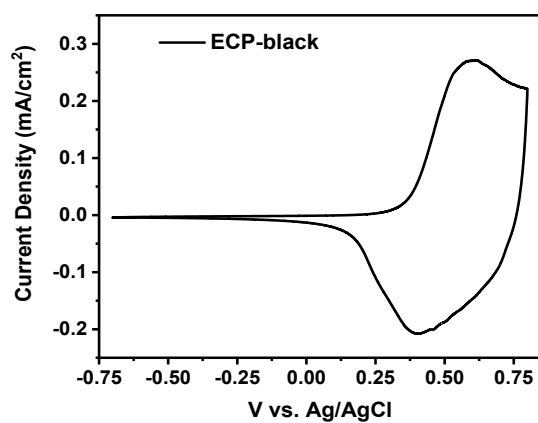


Figure S4. Cyclic voltammogram of the ECP-black in 0.2 M LiTFSI PC.

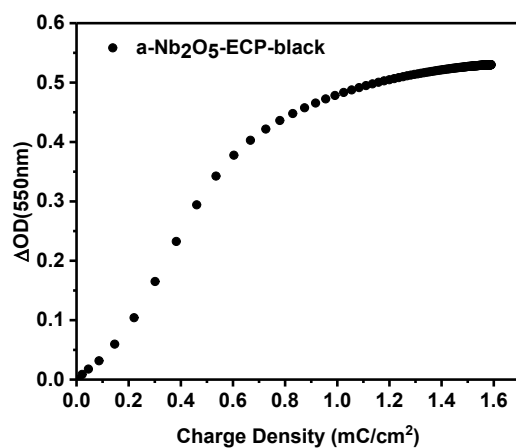


Figure S5. The change of optical density versus the charge density of the a-Nb₂O₅/ECP-black ECD.

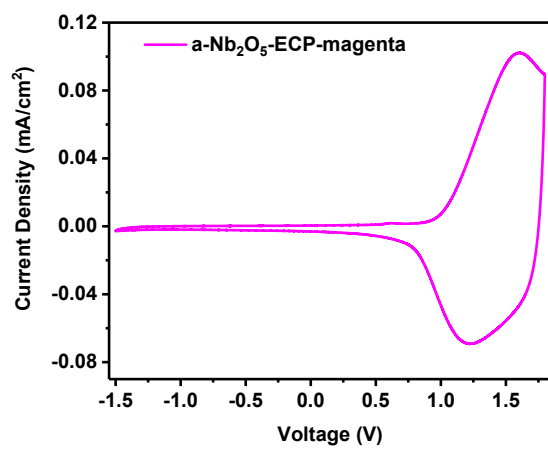


Figure S6. Cyclic voltammogram of the a-Nb₂O₅/ECP-magenta two-electrode cell in 0.2 M LiTFSI PC.